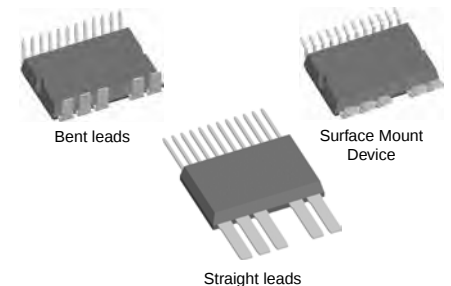
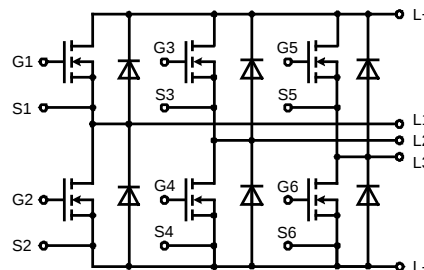


Three phase full Bridge with Trench MOSFETs in DCB isolated high current package

$$\begin{aligned}
V_{DSS} &= 55 \text{ V} \\
I_{D25} &= 160 \text{ A} \\
R_{DSon \text{ typ.}} &= 2.0 \text{ m}\Omega
\end{aligned}$$



MOSFETs			
Symbol	Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	55	V
V_{GS}		± 20	V
I_{D25}	$T_C = 25^\circ\text{C}$	160	A
I_{D90}	$T_C = 90^\circ\text{C}$	120	A
I_{F25}	$T_C = 25^\circ\text{C (diode)}$	135	A
I_{F90}	$T_C = 90^\circ\text{C (diode)}$	90	A

Applications

- AC drives
 - in automobiles
 - electric power steering
 - starter generator
 - in industrial vehicles
 - propulsion drives
 - fork lift drives
- in battery supplied equipment

Features

- MOSFETs in trench technology:
 - low R_{DSon}
 - optimized intrinsic reverse diode
- package:
 - high level of integration
 - high current capability 300 A max.
 - aux. terminals for MOSFET control
 - terminals for soldering or welding connections
 - isolated DCB ceramic base plate with optimized heat transfer
- Space and weight savings

Package options

- 3 lead forms available
 - straight leads (SL)
 - SMD lead version (SMD)
 - bent leads (BL)

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
$R_{DSon}^{1)}$	on chip level at $V_{GS} = 10 \text{ V}; I_D = 100 \text{ A}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		2.0 3.4	$\text{m}\Omega$ $\text{m}\Omega$
$V_{GS(th)}$	$V_{DS} = 20 \text{ V}; I_D = 1 \text{ mA}$	2		4	V
I_{DSS}	$V_{DS} = V_{DSS}; V_{GS} = 0 \text{ V}$		0.1	1	μA mA
I_{GSS}	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$			0.2	μA
Q_g Q_{gs} Q_{gd}	$V_{GS} = 10 \text{ V}; V_{DS} = 12 \text{ V}; I_D = 160 \text{ A}$		90 18 25		nC nC nC
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	inductive load $V_{GS} = 10 \text{ V}; V_{DS} = 24 \text{ V}$ $I_D = 100 \text{ A}; R_G = 39 \Omega;$ $T_J = 125^\circ\text{C}$		95 105 500 110		ns ns ns ns
E_{on}			0.12		mJ
E_{off}			0.52		mJ
E_{recoff}			0.012		mJ
R_{thJC} R_{thJH}	with heat transfer paste		1.2	0.9	K/W K/W

¹⁾ $V_{DS} = I_D \cdot (R_{DS(on)} + 2R_{Pin \text{ to Chip}})$

Source-Drain Diode

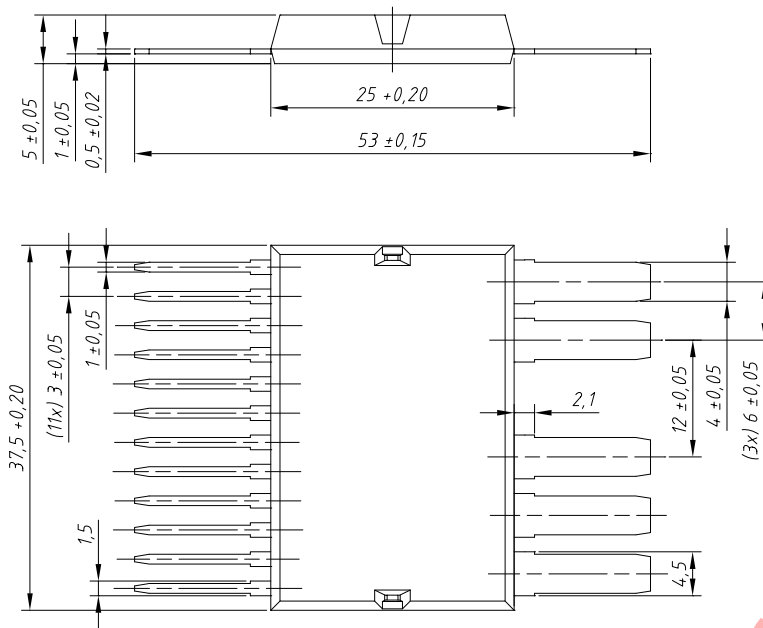
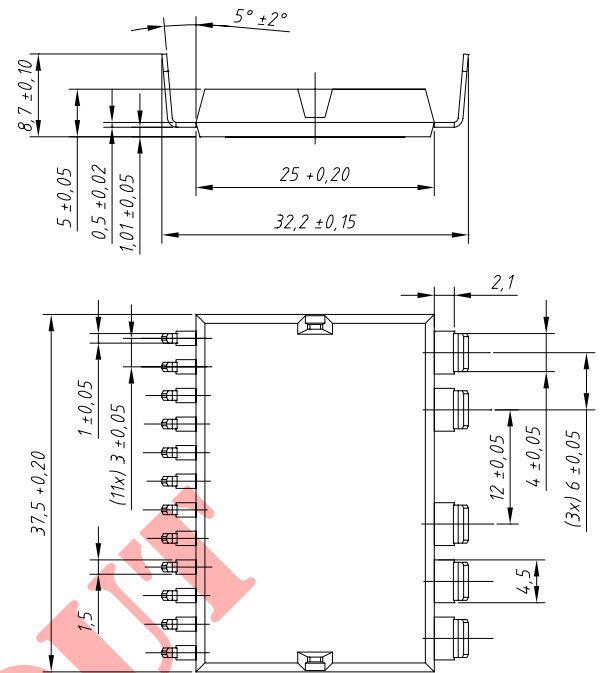
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_{SD}	(diode) $I_F = 100\text{ A}$; $V_{GS} = 0\text{ V}$		0.9	1.2
t_{rr}	$I_F = 100\text{ A}$; $-di_F/dt = 800\text{ A}/\mu\text{s}$; $V_R = 24\text{ V}$		60	ns
Q_{RM}			0,65	μC
I_{RM}			20	A

Component

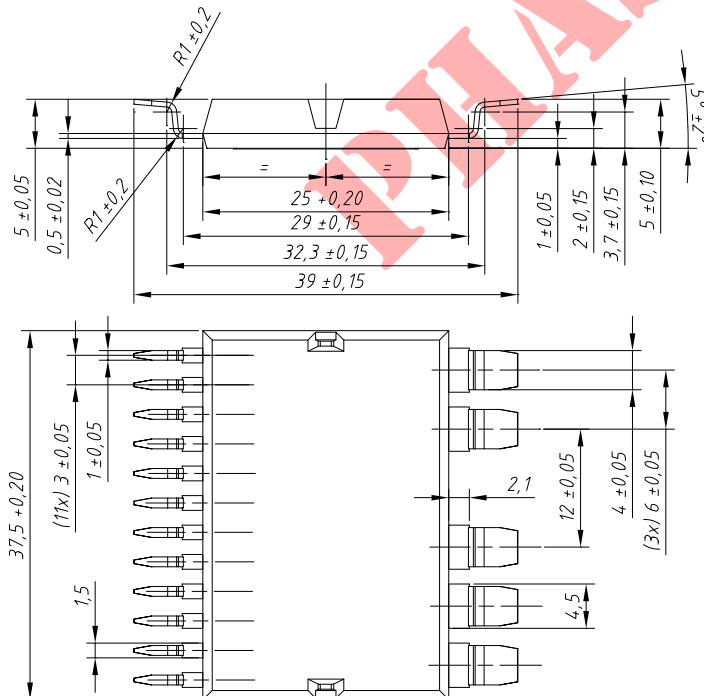
Symbol	Conditions	Maximum Ratings	
I_{RMS}	per pin in main current paths (P+, N-, L1, L2, L3) may be additionally limited by external connections	300	A
T_J		-40...+175	$^{\circ}\text{C}$
T_{stg}		-55...+125	$^{\circ}\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}$, 50/60 Hz, $f = 1\text{ minute}$	1000	V~
F_C	mounting force with clip	50 - 250	N

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{pin\text{ to chip}}^{1)}$			0.6	$\text{m}\Omega$
C_P	coupling capacity between shorted pins and mounting tab in the case		160	pF
Weight			25	g

¹⁾ $V_{DS} = I_D \cdot (R_{DS(on)} + 2R_{Pin\text{ to Chip}})$

Straight Leads GWM 160-0055P3-SL

Bent Leads GWM 160-0055P3-BL

Surface Mount Device
GWM 160-0055P3-SMD

Leads	Ordering Code & Packing Unit Marking	Part Marking	Code Key
Straight	GWM 160-0055P3 - SL	GWM 160-0055P3	502 829
SMD	GWM 160-0055P3 - SMD	GWM 160-0055P3	502 836
Bent	GWM 160-0055P3 - BL	GWM 160-0055P3	contact factory



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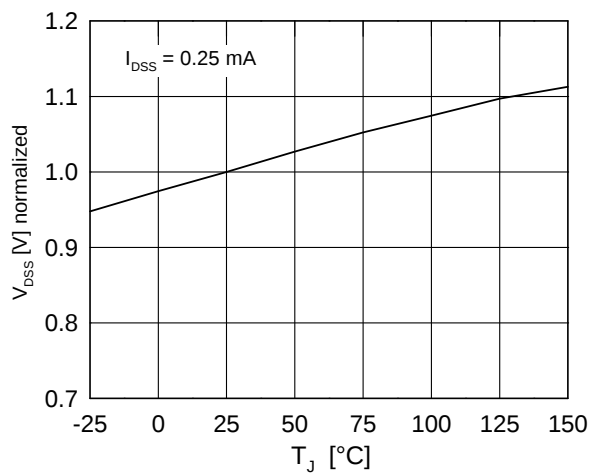


Fig. 1 Drain source breakdown voltage V_{DS} vs. junction temperature T_J

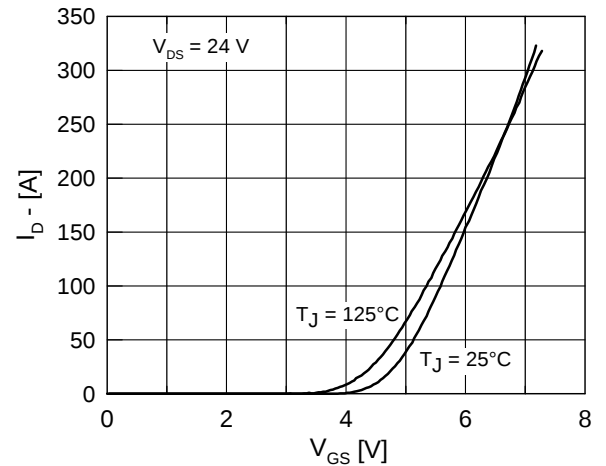


Fig. 2 Typical transfer characteristic

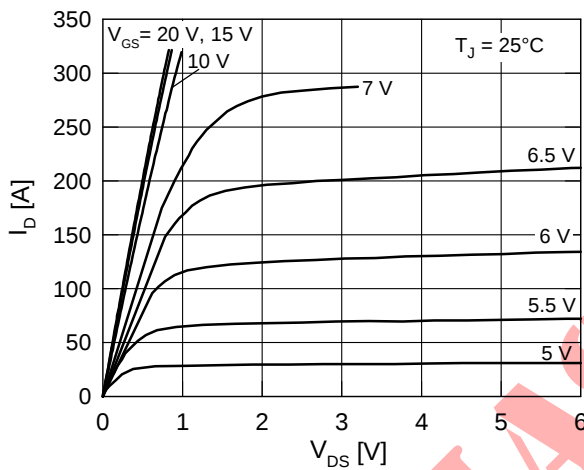


Fig. 3 Typical output characteristic

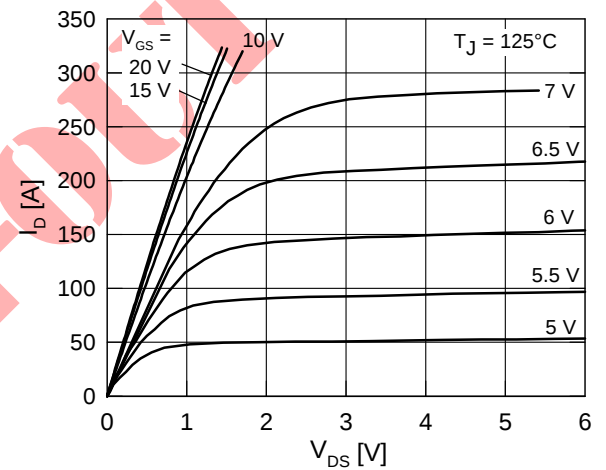


Fig. 4 Typical output characteristic

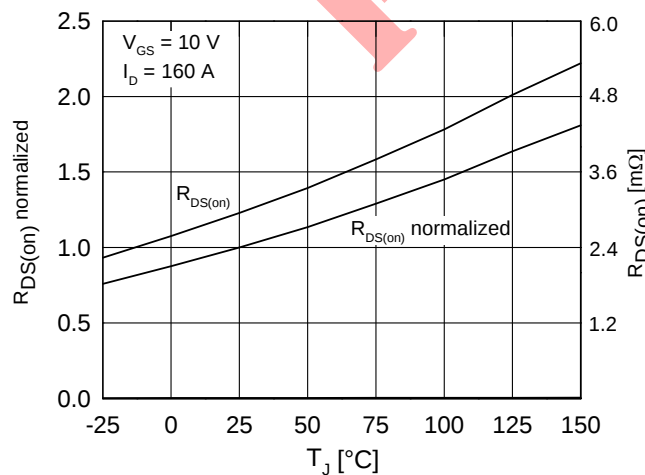


Fig. 5 Drain source on-state resistance $R_{DS(on)}$ versus junction temperature T_J

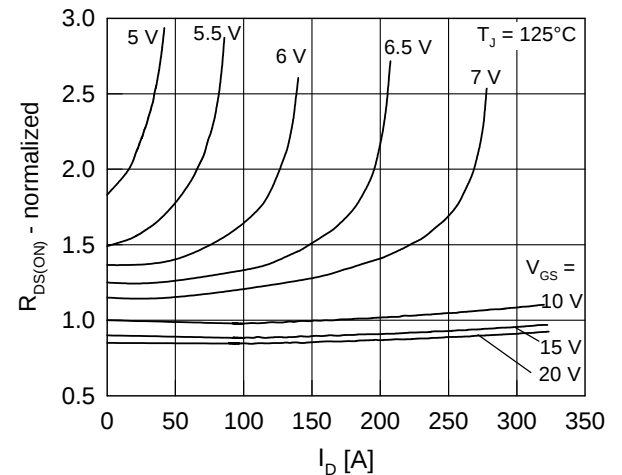


Fig. 6 Drain source on-state resistance $R_{DS(on)}$ versus I_D

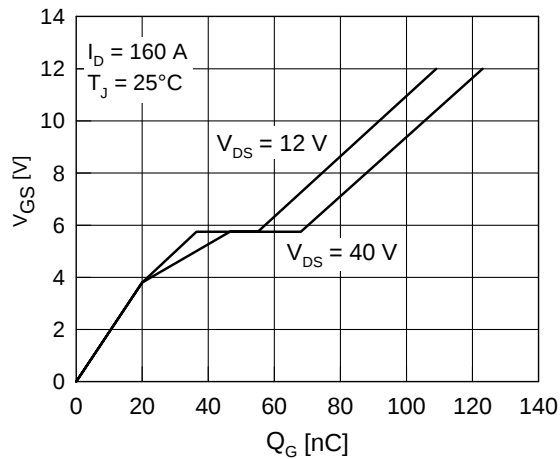


Fig. 7 Gate charge characteristic

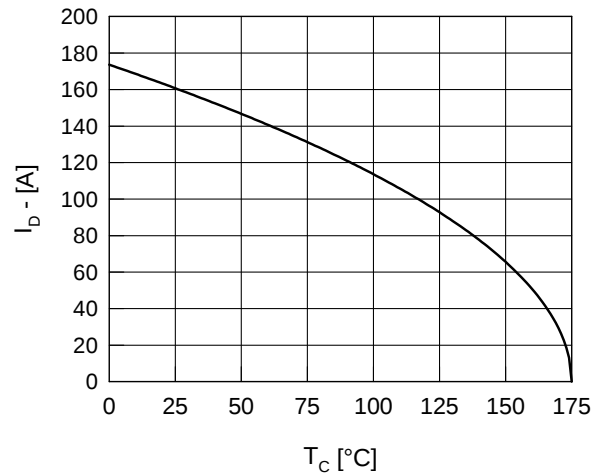


Fig. 8 Drain current I_D vs. case temperature T_C

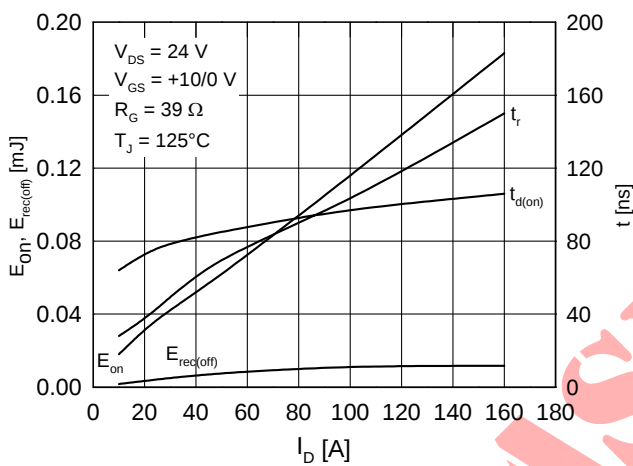


Fig. 9 Typ. turn-on energy & switching times vs. collector current, inductive switching

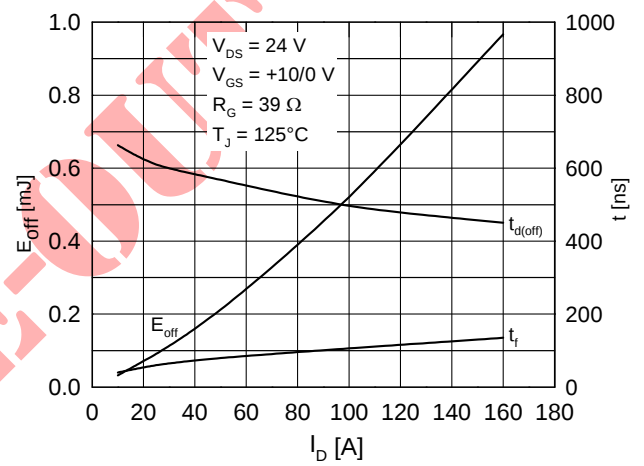


Fig. 10 Typ. turn-off energy & switching times vs. collector current, inductive switching

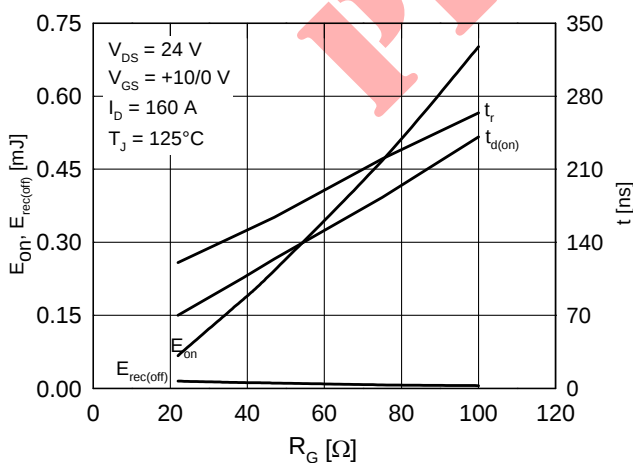


Fig. 11 Typ. turn-on energy & switching times vs. gate resistor, inductive switching

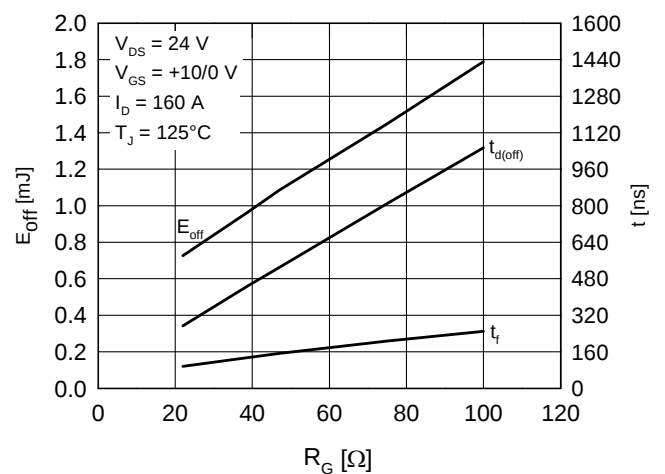


Fig. 12 Typ. turn-off energy & switching times vs. gate resistor, inductive switching

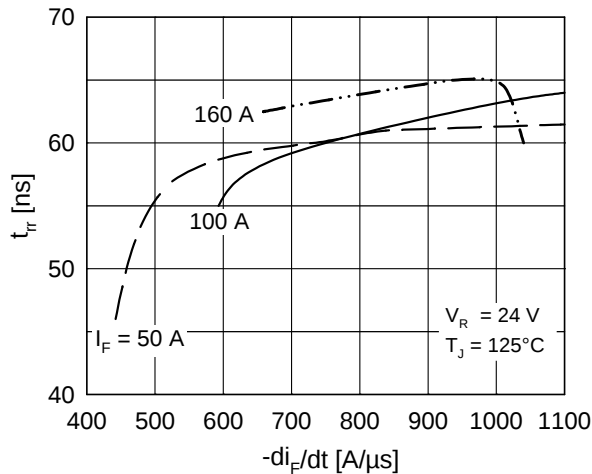


Fig. 13 Reverse recovery time t_{rr} of the body diode vs. di/dt

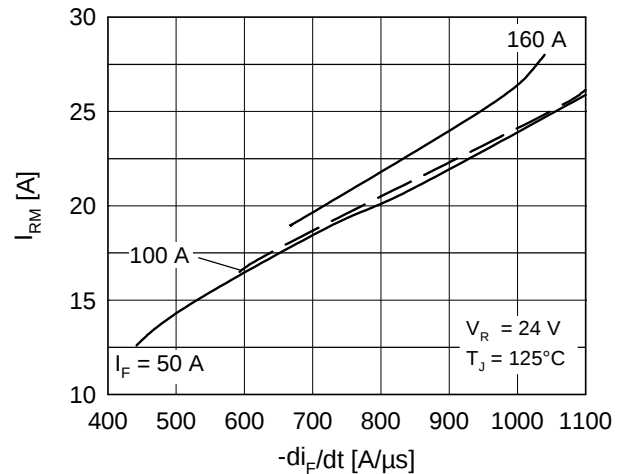


Fig. 14 Reverse recovery current I_{RM} of the body diode vs. di/dt

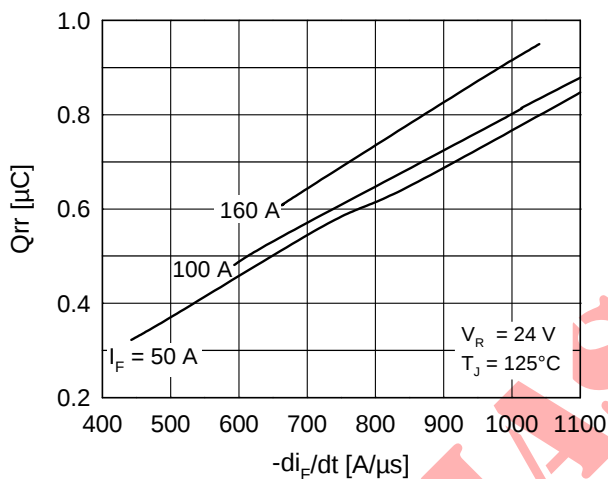


Fig. 15 Reverse recovery charge Q_{rr} of the body diode vs. di/dt

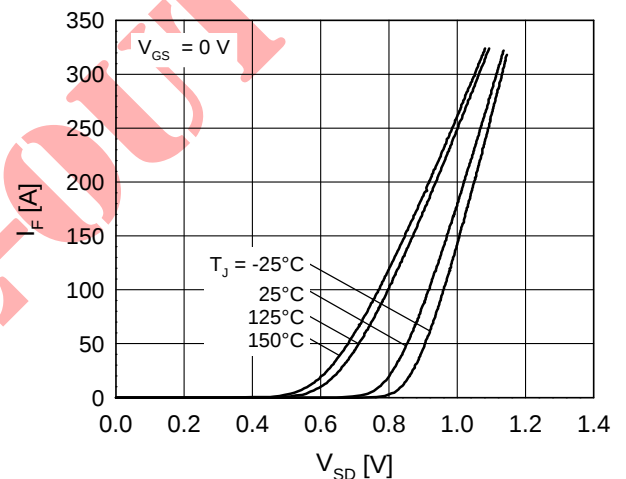


Fig. 16 Source drain diode current I_F vs. source drain voltage V_{SD} (body diode)

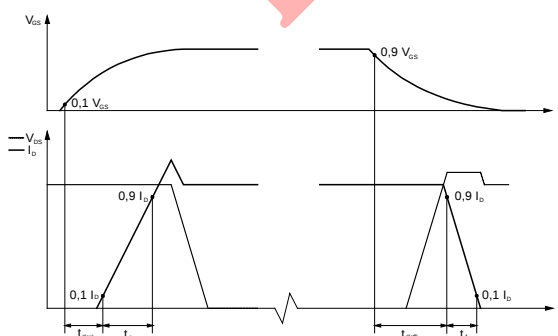


Fig. 17 Definition of switching times

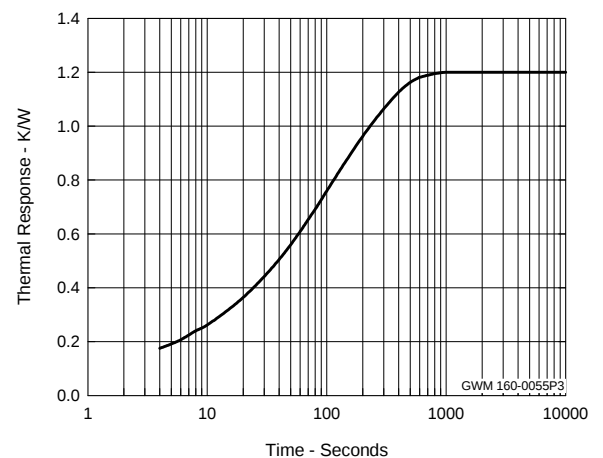


Fig. 18 Typ. thermal impedance junction to heatsink Z_{thJH} with heat transfer paste